



DMG3406L

N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

V _{(BR)DSS}	R _{DS(ON)} Max	I _D Max T _A = +25°C
001/	50mΩ @ V _{GS} = 10V	3.6A
30V	70mΩ @ V _{GS} = 4.5V	2.8A

Description and Applications

This MOSFET has been designed to minimize the on-state resistance (R_{DS(ON)}) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

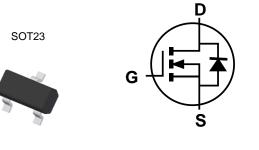
- Battery Charging
- Power Management Functions
- DC-DC Converters
- Portable Power Adaptors

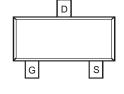
Features and Benefits

- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)

Mechanical Data

- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208
- Terminals Connections: See Diagram Below
- Weight: 0.008 grams (Approximate)





Top View

Internal Schematic

Top View Pin Out

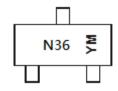
Ordering Information (Note 4)

Part Number	Case	Packaging
DMG3406L-7	SOT23	3000/Tape & Reel
DMG3406L-13	SOT23	10000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



N36 = Product Type Marking Code YM = Date Code Marking Y or \overline{Y} = Year (ex: C = 2015) M = Month (ex: 9 = September)

Date Code Key

Year	2014	4	2015		2016	20)17	2018		2019	2	2020
Code	В		С		D		E	F		G		Н
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



Maximum Ratings ($@T_A = +25^{\circ}C$, unless otherwise specified.)

Characteristic		Symbol	Value	Units	
Drain-Source Voltage			V_{DSS}	30	V
Gate-Source Voltage			V_{GSS}	±20	V
Continuous Drain Current (Note 6) $V_{GS} = 10V$ Steady $T_A = +25^{\circ}C$ State $T_A = +70^{\circ}C$			I_{D}	3.6 2.9	А
Pulsed Drain Current (Note 6) (Pulse width ≤10µ	S, Duty Cyc	I _{DM}	30	Α	
Maximum Body Diode Forward Current (Note 6)		I _s	1.4	А	

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 5)	P _D	0.77	W
Thermal Resistance, Junction to Ambient @T _A = +25°C (Note 5)	R _{eJA}	164	°C/W
Power Dissipation (Note 6)	P _D	1.4	W
Thermal Resistance, Junction to Ambient @T _A = +25°C (Note 6)	R _{eJA}	90	°C/W
Operating and Storage Temperature Range	$T_{J_i}T_{STG}$	-55 to +150	°C

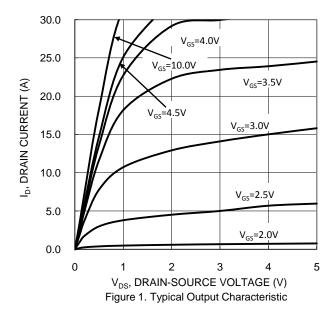
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

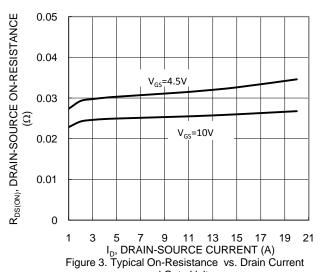
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)							
Drain-Source Breakdown Voltage	BV _{DSS}	30	_	_	V	$V_{GS} = 0V, I_D = 250\mu A$	
Zero Gate Voltage Drain Current T _J = +25°C	I _{DSS}	_	_	1.0	μΑ	$V_{DS} = 30V$, $V_{GS} = 0V$	
Gate-Source Leakage	I _{GSS}	_	_	±100	nA	$V_{GS} = \pm 20V$, $V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	$V_{GS(TH)}$	1.0	_	2.0	V	$V_{DS} = V_{GS}$, $I_D = 250\mu A$	
Static Drain-Source On-Resistance	D	_	25	50	mΩ	$V_{GS} = 10V, I_D = 3.6A$	
Static Dialii-Source Oil-Resistance	R _{DS (ON)}		31	70	11122	$V_{GS} = 4.5V, I_D = 2.8A$	
Diode Forward Voltage	V_{SD}	_	0.75	1.0	V	$V_{GS} = 0V$, $I_S = 1A$	
DYNAMIC CHARACTERISTICS (Note 8)							
Input Capacitance	C_{iss}	_	495	_	pF		
Output Capacitance	Coss	_	50		pF	$V_{DS} = 15V, V_{GS} = 0V,$ f = 1.0MHz	
Reverse Transfer Capacitance	C_{rss}	_	43	_	pF		
Gate Resistance	R_{g}	_	2.0		Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$	
Total Gate Charge (V _{GS} = 4.5V)	Q_g		5.3		nC		
Total Gate Charge (V _{GS} = 10V)	Q_g	_	11.2		nC	V _{DS} = 15V. I _D = 3.6A	
Gate-Source Charge	Q_{gs}		1.2		nC	V _{DS} = 13V, I _D = 3.0A	
Gate-Drain Charge	Q_{gd}	_	1.9		nC		
Turn-On Delay Time	t _{D(ON)}	_	2.3		ns		
Turn-On Rise Time	t _R	_	3.3	_	ns	$V_{DD} = 15V, V_{GS} = 10V,$	
Turn-Off Delay Time	$t_{D(OFF)}$		10.3		ns	$R_L = 2.2\Omega$, $R_G = 3\Omega$	
Turn-Off Fall Time	t _F		2.3		ns		

Notes

- 5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
- 6. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1 inch square copper plate.
- 7. Short duration pulse test used to minimize self-heating effect.
- 8. Guaranteed by design. Not subject to product testing.







and Gate Voltage

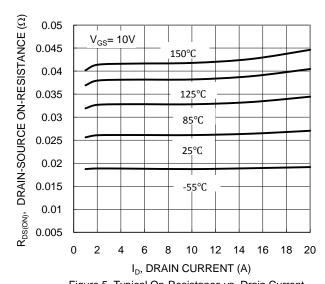


Figure 5. Typical On-Resistance vs. Drain Current and Temperature

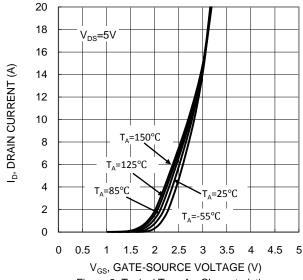
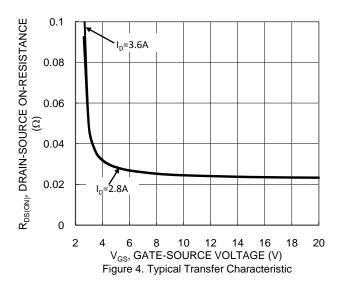


Figure 2. Typical Transfer Characteristic



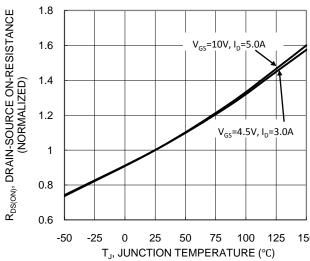
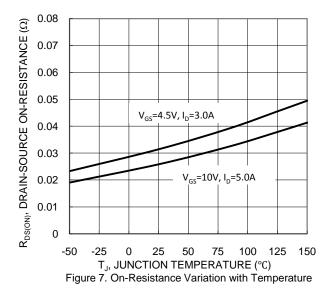
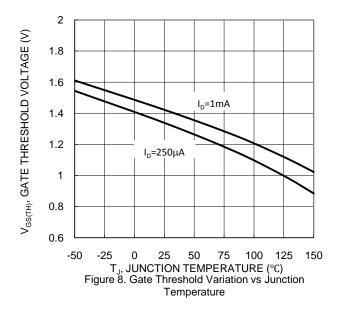
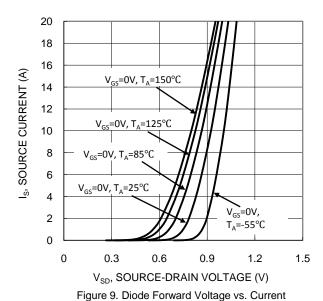


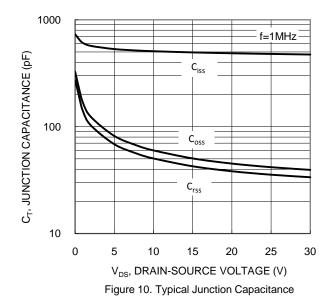
Figure 6. On-Resistance Variation with Temperature

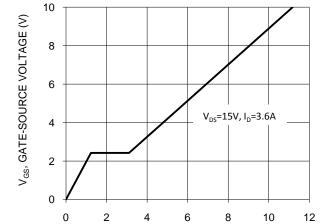




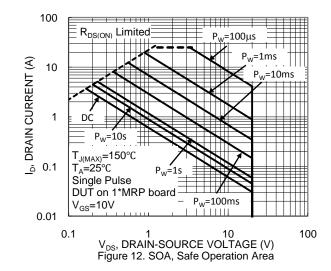








Qg,TOTAL GATE CHARGE (nC) Figure 11. Gate Charge





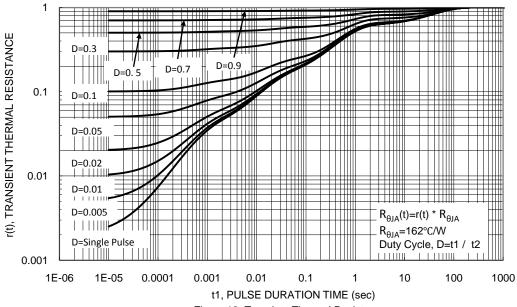
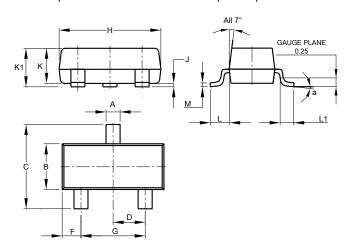


Figure 13. Transient Thermal Resistance

Package Outline Dimensions

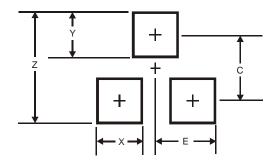
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



SOT23							
Dim	Min	Max	Тур				
Α	0.37	0.51	0.40				
В	1.20	1.40	1.30				
C	2.30	2.50	2.40				
D	0.89	1.03	0.915				
F	0.45	0.60	0.535				
G	1.78	2.05	1.83				
Η	2.80	3.00	2.90				
J	0.013	0.10	0.05				
K	0.890	1.00	0.975				
K1	0.903	1.10	1.025				
L	0.45	0.61	0.55				
L1	0.25	0.55	0.40				
М	0.085	0.150	0.110				
α	α 8°						
All Dimensions in mm							

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
Z	2.9
X	0.8
Y	0.9
С	2.0
E	1.35



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